

IMPROVED CURRENT MODE PWM CONTROLLER

Check for Samples: UC2856Q

FEATURES

- Pin-for-Pin Compatible With the UC2846
- 65-ns Typical Delay From Shutdown to Outputs and 50-ns Typical Delay From Sync to Outputs
- Improved Current Sense Amplifier With Reduced Noise Sensitivity
- Differential Current Sense With 3-V Common Mode Range
- Trimmed Oscillator Discharge Current for Accurate Deadband Control
- Accurate 1-V Shutdown Threshold
- High Current Dual Totem Pole Outputs (1.5-A peak)
- TTL Compatible Oscillator SYNC Pin Thresholds
- 4-kV ESD Protection

DW PACKAGE (TOP VIEW) CL SS I 16 ☐ SHUTDOWN 2 15 VREF \square T VIN 14 CS- □ T BOUT CS+ □ 13 ☐ VC EA+ \Box 12 ☐ GND AOUT EA- \Box 11 COMP I 10 CT \square 8 9 ☐ RT

P0008-01

DESCRIPTION

The UC2856 is a high performance version of the popular UC2846 series of current mode controllers, and is intended for both design upgrades and new applications where speed and accuracy are important. All input to output delays have been minimized, and the current sense output is slew rate limited to reduce noise sensitivity. Fast 1.5-A peak output stages have been added to allow rapid switching of power FETs.

A low impedance TTL compatible sync output has been implemented with a 3-state function when used as a sync input.

Internal chip grounding has been improved to minimize internal *noise* caused when driving large capacitive loads. This, in conjunction with the improved differential current sense amplifier, results in enhanced noise immunity.

Other features include a trimmed oscillator current (8%) for accurate frequency and dead time control; a 1 V, 5% shutdown threshold; and 4 kV minimum ESD protection on all pins.

ORDERING INFORMATION⁽¹⁾

TA	PAG	CKAGE	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 125°C	SOP-DW	Tape and reel	UC2856QDWR	UC2856Q

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



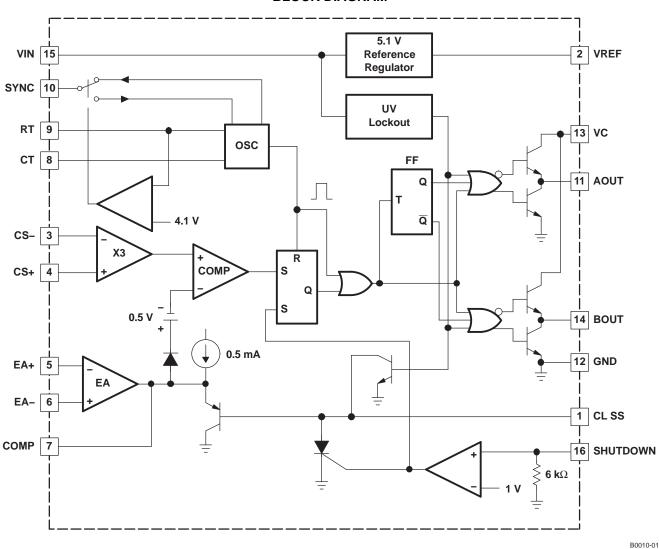
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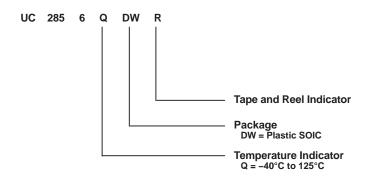


These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

BLOCK DIAGRAM



ORDERING INFORMATION





ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1) (2)

			UNIT
	Supply voltage		40 V
	Collector supply voltage		40 V
	Outrot summer (sink an accuracy	DC	0.5 A
C	Output current (sink or source)	Pulse (0.5 ms)	2 A
	Error amplifier input voltage		−0.3 V to VIN
	Shutdown input voltage		–0.3 V to 10 V
	Current sense input voltage		−0.3 V to 3 V
	SYNC output current		±10 mA
	Error amplifier output current		-5 mA
	Soft start sink current		50 mA
	Oscillator charging current		5 mA
	Dower discination	T _A = 25°C	1 W
	Power dissipation	T _C = 25°C	2 W
ГЈ	Operating junction temperature rar	ge	–55°C to 150°C
T _{stg}	Storage temperature range		−65°C to 150°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $T_A = -40$ °C to 125°C, VIN = 15 V, RT = 10 k Ω , CT = 1 nF, and $T_A = T_J$ (unless otherwise stated)⁽¹⁾

PARAMETER	TEST C	MIN	TYP	MAX	UNIT	
REFERENCE SECTION	<u>, </u>					
Output voltage	I _O = 1 mA,	T _J = 25°C	5.05	5.1	5.15	V
Line regulation voltage	VIN = 8 V to 40 V				20	mV
Load regulation voltage	$I_O = -1 \text{ mA to } -10 \text{ mA}$				15	mV
Total output variation	Line, Load, and Tempera	ature	5		5.2	V
Output noise voltage	f = 10 Hz to 10 kHz,	$T_J = 25^{\circ}C$		50		μV
Long term stability	1000 hours, (2)	$T_J = 25^{\circ}C$		5	25	mV
Short circuit current	VREF = 0 V		-25	-4 5	-65	mA
OSCILLATOR SECTION					<u> </u>	
Lettel and a second	T _J = 25°C		180	200	220	1.1.1-
Initial accuracy	T _J = Full range	T _J = Full range				kHz
Voltage stability	VIN = 8 V to 40 V				2%	
D'ack annual annual	VCT = 2 V,	T _J = 25°C	7.5	8	8.8	
Discharge current	VCT = 2 V		6.7	8	8.8	mA
Sync output high level voltage	I _O = -1 mA		2.4	3.6		V
Sync output low level voltage	I _O = 1 mA			0.2	0.4	V
Sync input high level voltage	CT = 0 V, RT = VREF		2	1.5		V
Sync input low level voltage	CT = 0 V, RT = VREF			1.5	0.8	V
Sync input current	CT = 0 V, RT = VREF,V	SYNC = 5 V		1	10	μA
Sync delay to outputs	CT = 0 V RT = VREF, V	SYNC = 0.8 V to 2 V		50	100	ns

⁽¹⁾ All voltages are with respect to GND. Currents are positive into, negative out of the specified terminal.

⁽²⁾ Unless otherwise indicated, voltages are reference to ground and currents are positive into and negative out of the specified terminals.

⁽²⁾ This parameter, although specified over the recommended operating conditions, is not 100% tested in production.



ELECTRICAL CHARACTERISTICS (continued)

 $T_A = -40$ °C to 125°C, VIN = 15 V, RT = 10 k Ω , CT = 1 nF, and $T_A = T_J$ (unless otherwise stated)⁽¹⁾

PARAMETER	TEST COM	NDITIONS	MIN	TYP	MAX	UNIT
ERROR AMPLIFIER SECTION						
Input offset voltage	V _{CM} = 2 V				5	mV
Input bias current					-1	μΑ
Input offset current					500	nA
Common mode range	VIN = 8 V to 40 V		0		VIN-2	V
Open loop gain	$V_0 = 1.2 \text{ V to 3 V}$		80	100		dB
Unity gain bandwidth	$T_J = 25^{\circ}C$		1	1.5		MHz
CMRR	$V_{CM} = 0 V \text{ to } 38 V,$	VIN = 40 V	75	100		dB
PSRR	VIN = 8 V to 40 V		80	100		dB
Output sink current	$V_{ID} = -15 \text{ mV}$	$V_{COMP} = 1.2 V$	5	10		mA
Output source current	$V_{ID} = 15 \text{ mV}$	$V_{COMP} = 2.5 V$	-0.4	-0.5		mA
High-level output voltage	$V_{ID} = 50 \text{ mV},$	R_L (COMP) = 15 k Ω	4.3	4.6	4.9	V
Low-level output voltage	$V_{ID} = -50 \text{ mV},$	R_L (COMP) = 15 k Ω		0.7	1	V
CURRENT SENSE AMPLIFIER SECTION						
Amplifier gain	$V_{CS-} = 0 V$,	CL SS Open ^{(3) (4)}	2.5	2.75	3	V/V
Maximum differential input signal (V _{CS+} – V _{CS-})	CL SS Open 3,	R_L (COMP) = 15 k Ω	1.1	1.2		V
Input offset voltage	V _{CL SS} = 0.5 V	COMP open ⁽³⁾		5	35	mV
CMRR	$V_{CM} = 0 V to 3 V$		60			dB
PSRR	VIN = 8 V to 40 V		60			dB
Input bias current	$V_{CL SS} = 0.5 V$,	COMP open ⁽³⁾			-1	μA
Input offset current	$V_{CL SS} = 0.5 V,$	COMP open ⁽³⁾			1	mA
Input common mode range			0		3	V
Delay to outputs	V _{EA+} = VREF, EA- = 0 V,	CS+ - CS- = 0 V to 1.5 V		120	250	ns
CURRENT LIMIT ADJUST SECTION						
Current limit offset	$V_{CS-} = 0 \text{ V}, V_{CS+} = 0 \text{ V},$	COMP Open ⁽³⁾	0.4	0.5	0.6	V
Input bias current	V _{EA+} = VREF,	V _{EA-} = 0 V		-10	-30	μA
SHUTDOWN TERMINAL SECTION	•				·	
Threshold voltage			0.95	1.00	1.05	V
Input voltage range			0		5	V
Minimum latching current (I _{CL SS})			(⁵⁾ 3	1.5		mA
Maximum non-latching current (I _{CL SS})				⁽⁶⁾ 1.5	0.8	mA
Delay to outputs	V _{SHUTDOWN} = 0 V to 1.3 V			65	110	ns
OUTPUT SECTION						
Collector-emitter voltage			40			V
Off-state bias current	VC = 40 V				250	μA
Output law law law law law as	I _{OUT} = 20 mA			0.1	0.5	
Output low level voltage	I _{OUT} = 200 mA			0.5	2.6	V
Output himb lavel value	I _{OUT} = -20 mA		12.5	13.2		
Output high level voltage	I _{OUT} = -200 mA		12	13.1		V
Rise time	C1 = 1 nF			40	80	ns
Fall time	C1 = 1 nF			40	80	ns
UVLO low saturation	VIN = 0 V,	I _{OUT} = 20 mA		0.8	1.5	V

⁽³⁾ Parameter measured at trip point of latch with VEA+ = VREF, VEA- = 0 V. $G = \frac{\Delta V_{COMP}}{\Delta V_{CS}}; \ \Delta V_{CS} - = \ 0 \ V \ 1 \ V.$ (4) Amplifier gain defined as:

$$G = \frac{\Delta V_{COMP}}{\Delta V_{CS}}$$
; $\Delta V_{CS} - = 0 V 1 V$.

Amplifier gain defined as:

Current into CL SS assured to latch circuit into shutdown state. (5)

Current into CL SS assured not to latch circuit into shutdown state. (6)



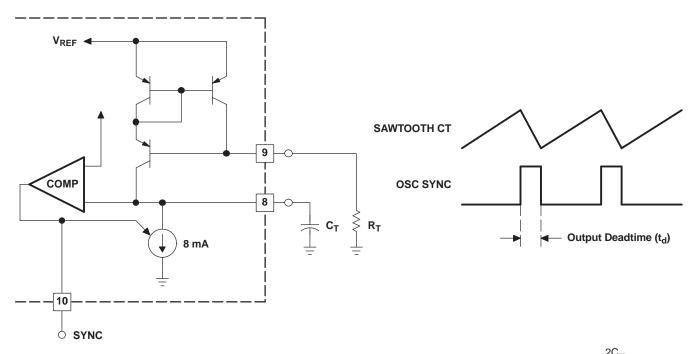
ELECTRICAL CHARACTERISTICS (continued)

 $T_A = -40$ °C to 125°C, VIN = 15 V, RT = 10 k Ω , CT = 1 nF, and $T_A = T_J$ (unless otherwise stated)⁽¹⁾

		·			
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
PWM SECTION					
Maximum duty cycle		45%	47%	50%	
Minimum duty cycle				0%	
UNDERVOLTAGE LOCKOUT SECTION					
Startup threshold			7.7	8	
Threshold hysterisis			0.7		
TOTAL STANDBY CURRENT				•	
Supply current			18	23	mA



APPLICATION AND OPERATION INFORMATION



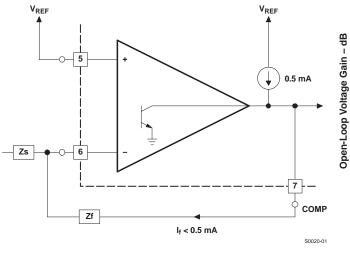
NOTE: Output deadtime is determined by the size of the external capacitor, C_T , according to the formula: For large values of R_T : $Td = 250 \ C_T$

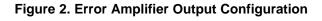
Oscillator frequency is approximated by the formula: $f_T = \frac{2}{R_T \times C_T}$

S0019-01

Figure 1. Oscillator Circuit

NOTE: Error Amplifier can source up to 0.5 mA.





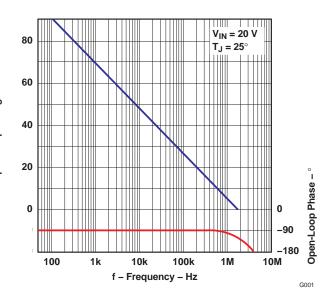


Figure 3. Error Amplifier Gain and Phase vs Frequency



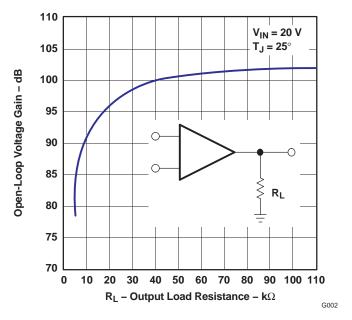
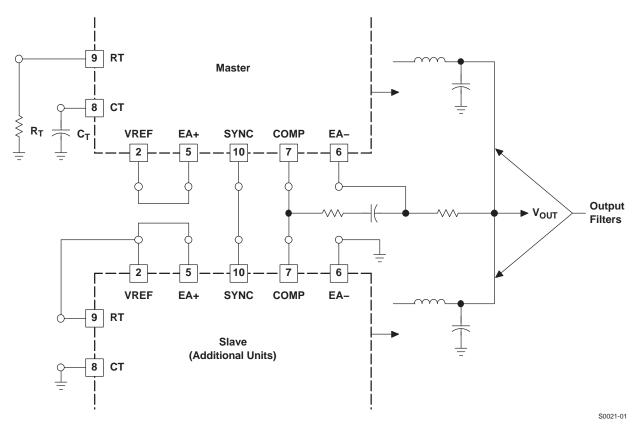


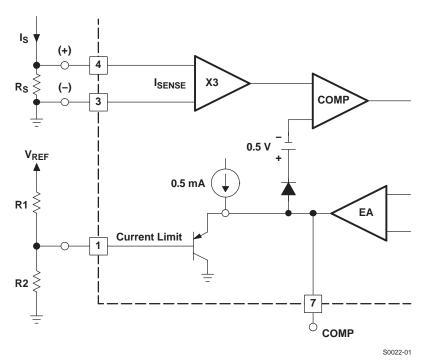
Figure 4. Error Amplifier Open-Loop DC Gain vs Load Resistance



NOTE: Slaving allows parallel operation of two or more units with equal current sharing.

Figure 5. Parallel Operation

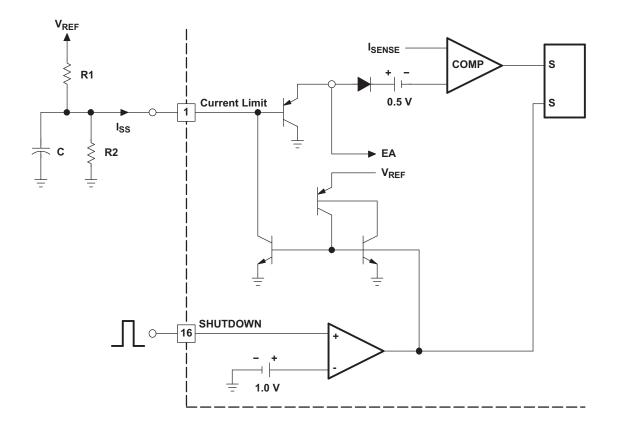


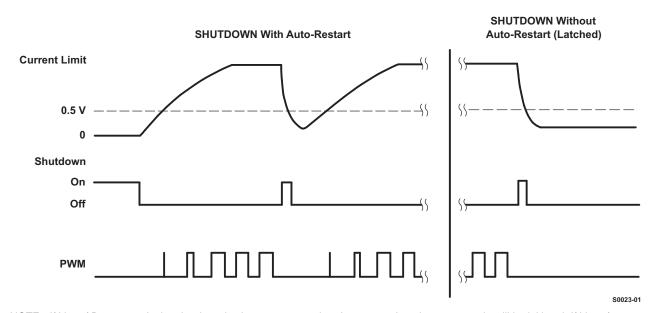


 $I_{S} = \frac{\left(\text{R2} \times \frac{\text{V}_{REF}}{\text{R1} + \text{R2}}\right) - 0.5}{3\text{R}_{S}}$ NOTE: Peak current (I_S) is determined by the formula:

Figure 6. Pulse by Pulse Current Limiting







NOTE: If V_{REF} / R1 < 0.8 mA, the shutdown latch commutates when I_{SS} = 0.8 mA and a restart cycle will be initiated. If V_{REF} / R1 > 3 mA, the device will latch off until power is recycled.

Figure 7. Shutdown



REVISION HISTORY

Cr	nanges from Original (November 2004) to Revision A	Pag	e
•	Changed the polarity of the comparator connected to pin 16 in Figure 7		9



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
UC2856QDWR	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	UC2856Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

www.ti.com 3-Jun-2022

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
UC2856QDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

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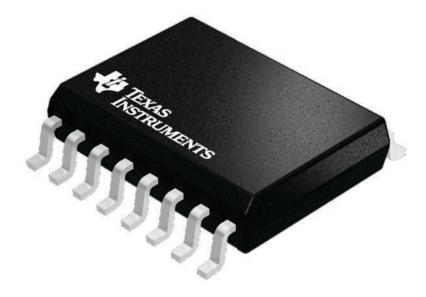
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
UC2856QDWR	SOIC	DW	16	2000	356.0	356.0	35.0

7.5 x 10.3, 1.27 mm pitch

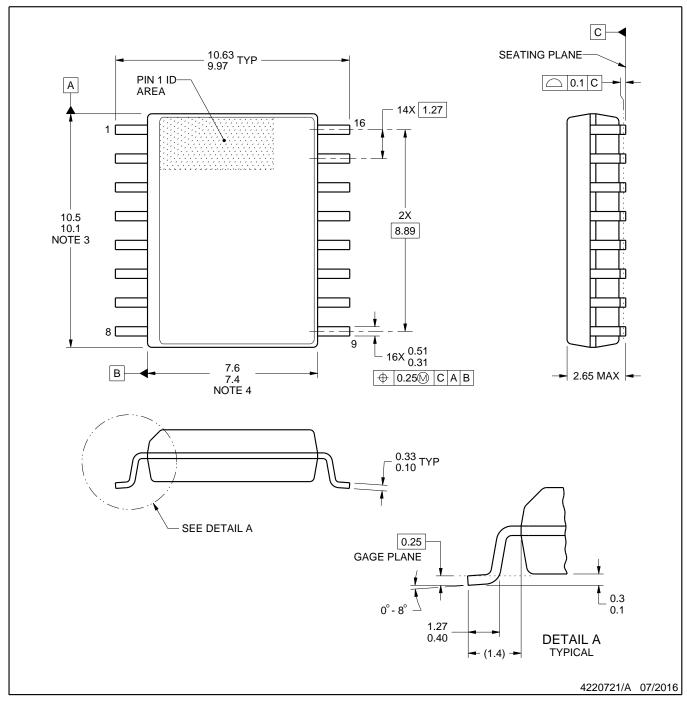
SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





SOIC



NOTES:

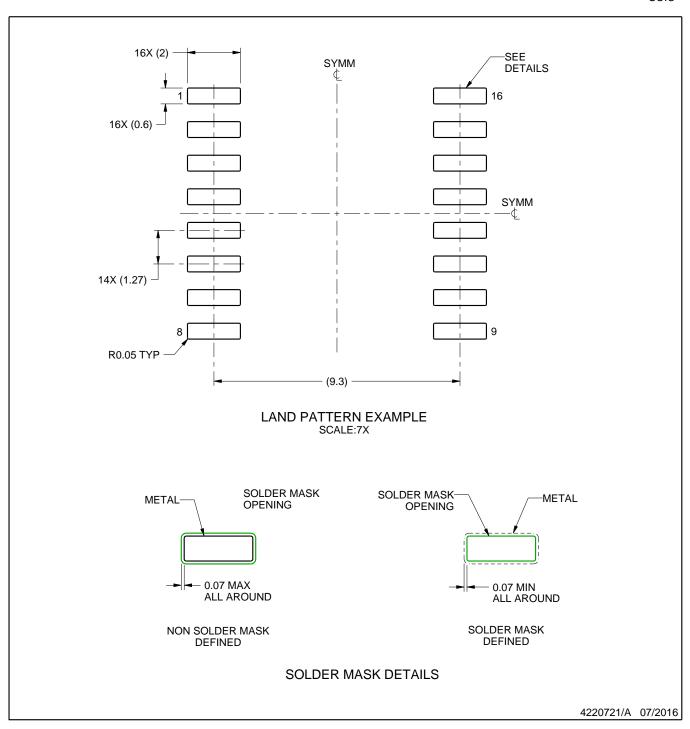
- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.



SOIC



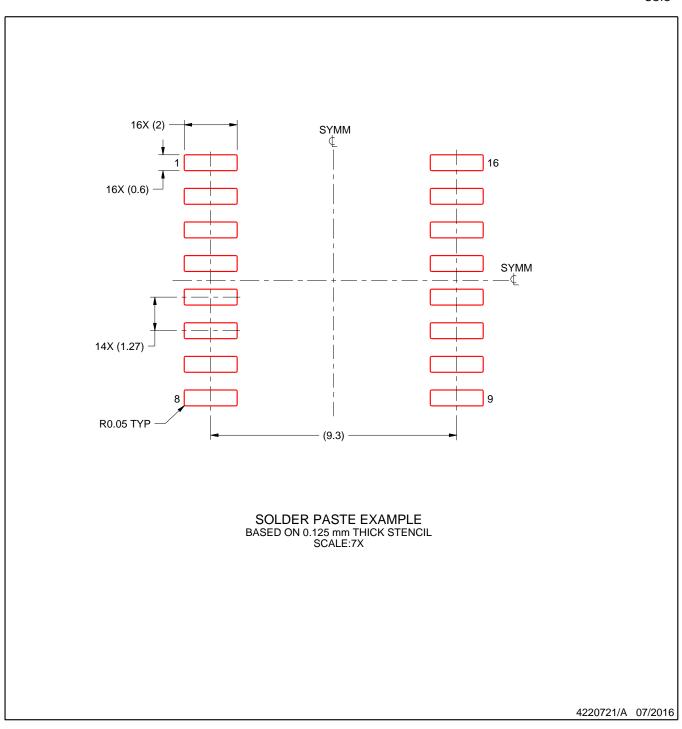
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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